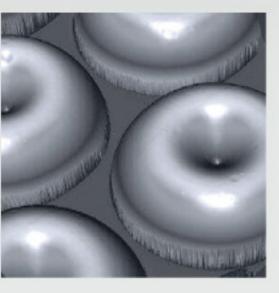


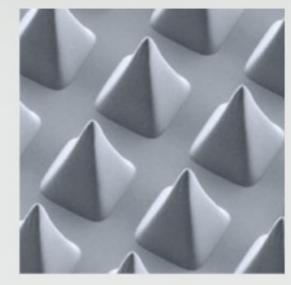
# DWL 2000 GS / DWL 4000 GS

# THE PROFESSIONAL GRAYSCALE LITHOGRAPHY TOOL





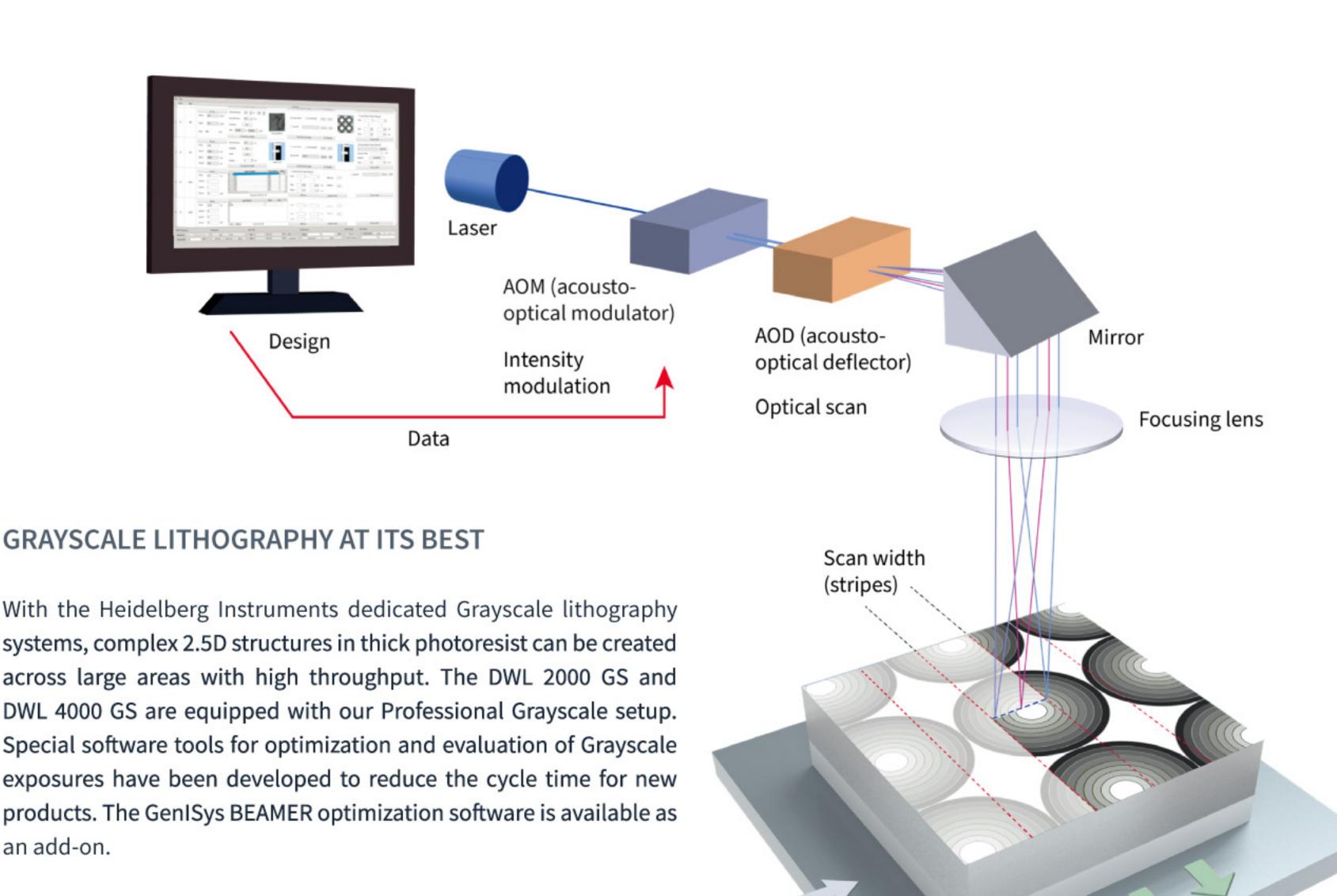




# DWL 2000 GS / DWL 4000 GS

## THE PROFESSIONAL GRAYSCALE LITHOGRAPHY TOOL

The expert Grayscale (GS) Lithography tools DWL 2000 GS and DWL 4000 GS provide advanced Grayscale technology that satisfies the highest industrial standards. Grayscale Lithography – in contrast to traditional binary laser lithography – produces 2.5D or freeform topographies such as micro-lenses or sloping features like blazed gratings. This technology plays a crucial role in micro-optical applications, producing for example identifiers such as security markers or holograms. It is also frequently employed for large area modifications of surfaces that serve as light modifiers, for example, reflectors.



Grayscale exposure strategy

Substrate

motion

**HIGH-STABILITY SYSTEM SETUP** 

and life sciences.

high-precision air-bearing stage system guarantee the quality and position accuracy of the exposed structures.

To ensure the lowest surface roughness possible and shape

conformity, the systems support up to 1023 gray levels. The most

common Grayscale applications include the fabrication of wafer-

level optics used for telecommunication or illumination market

segments, where our systems are being used by some of the largest

multinational corporations. Other applications include display

manufacturing as well as device fabrication in the fields of biology

A high-resolution interferometer monitors the position of the stage at all times. To ensure maximum stability, an advanced climate You can choose between four available write modes to optimize the control provides constant temperature stability during operation. system performance for different applications.

A fixed optical setup, a reliable real-time autofocus system, and a Additional software is used to compensate for any remaining variation in the mechanical structures or the environmental parameters. The systems are equipped with an integrated CCD camera and an overview camera for easy alignment to existing features.

### **HOLOGRAMS**

Hologram: Resist: AZ 1500

### **DIFFUSORS AND REFLECTORS**

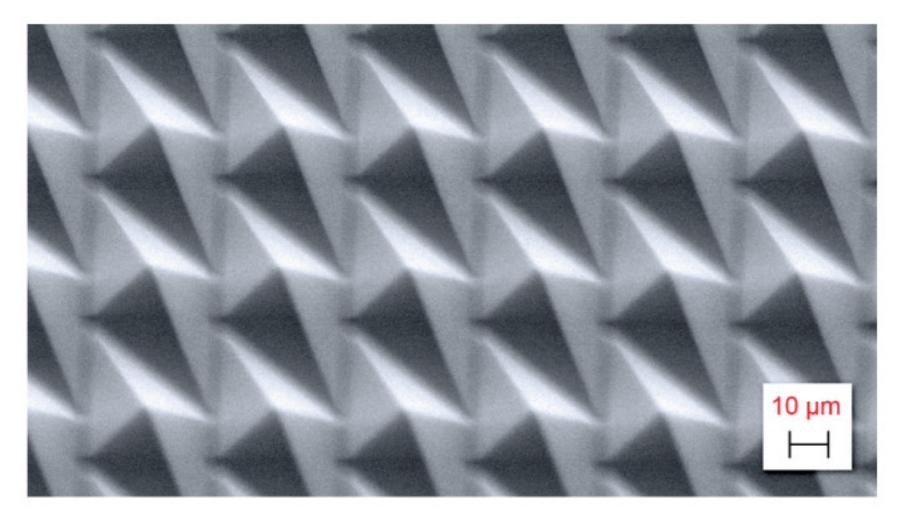
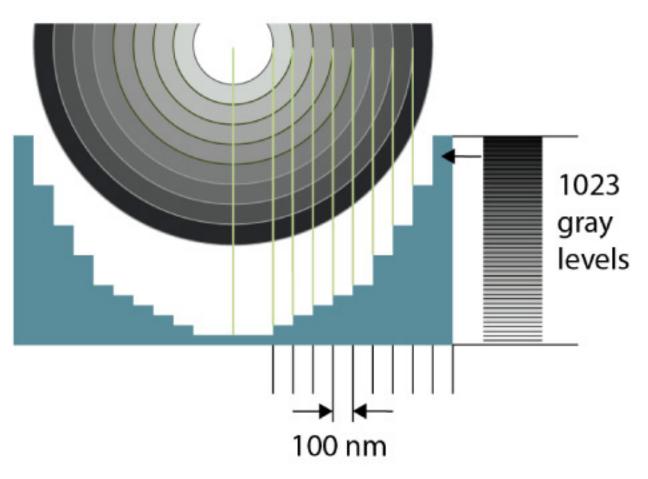
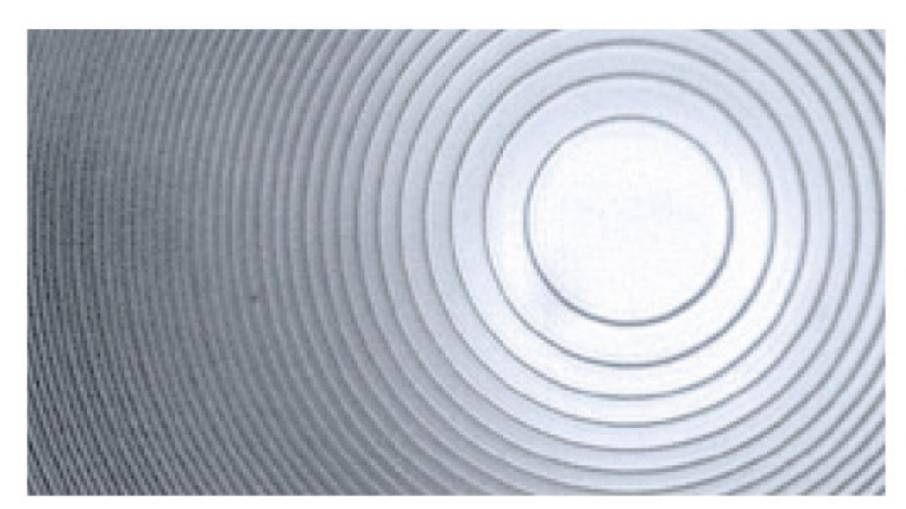


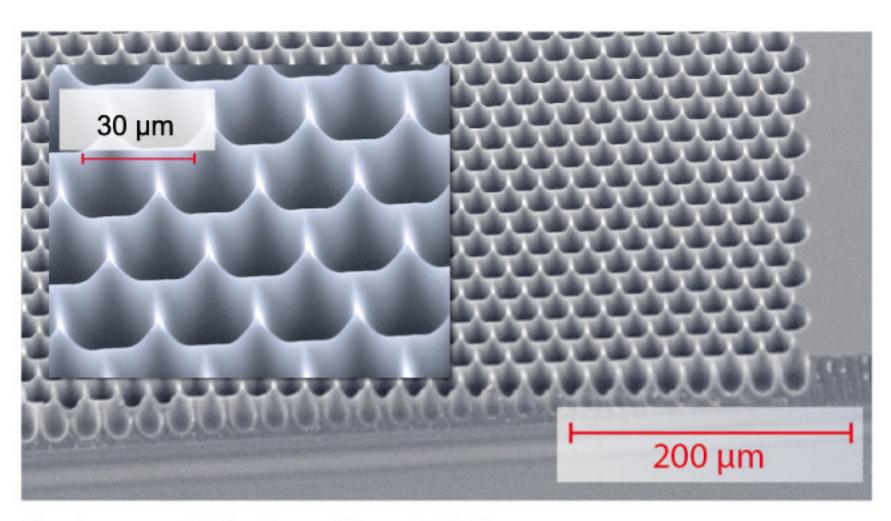
Image courtesy of karmic.ch



### FRESNEL LENSES

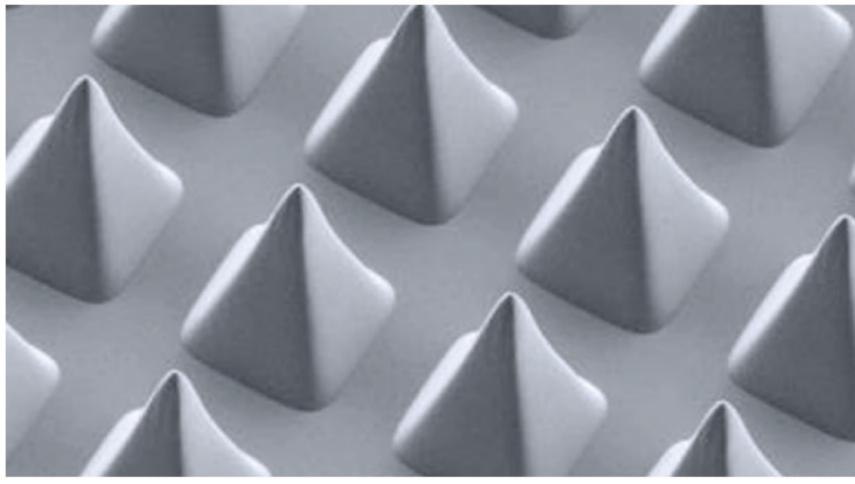


#### MICROLENSES AND MICROLENS ARRAYS

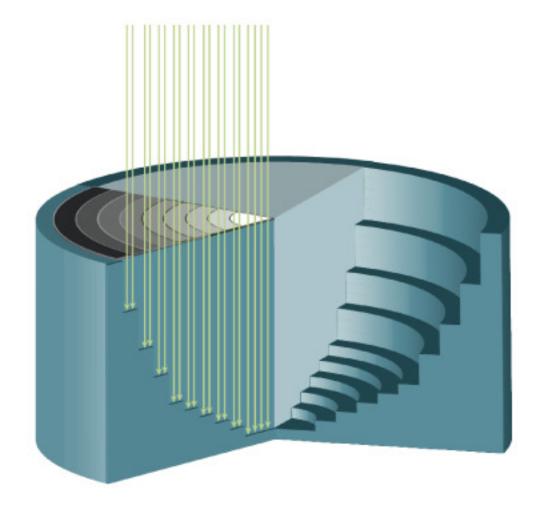


Microlens array: Width of lenses 20  $\mu m$ , depth 30  $\mu m$ 

### **TEXTURED SURFACES**



Resist: AZ 4562, thickness 54  $\mu m$ . Pyramid height 50  $\mu m$ , distance between pyramids 8  $\mu m$ 



The gray value model: From 3D-CAD to light intensity. The input data defines a 3D topography. Each position in the 3D input data is mapped to the gray values according to the exposure pixel grid. Each gray value corresponds to an individual exposure intensity level. The system determines the pixel-by-pixel exposure depth accordingly.

### PROFESSIONAL GRAYSCALE: HIGHLIGHTS

- Create complex topographies for micro-optical components or other Grayscale applications: Optical quality surfaces (roughness down to 5 nm) can be produced
- File formats: DXF, BMP, STL and X,Y,Z-ASCII
- Expose CAD files with up to 1023 levels
- Extensive software package:
  - Manipulate and combine CAD files to create complex patterns
  - Optimize layouts to maximize structure quality and minimize exposure time
- Optional GenISys BEAMER and LAB software data optimization and simulation

# DWL 2000 GS / DWL 4000 GS

## SYSTEM SPECIFICATIONS

Writing performance - Grayscale           Overlay [3σ, nm] (over 8" x 8")         300           Pixel Grid Grayscale [nm]         100         200         250         500         1000           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         1000           Exposure Time DWL 2000 GS: For 200 mm x 200 mm [hours]         51         13.5         9         2.5         0.8           Exposure Time DWL 2000 GS: For 400 mm x 400 mm [hours]         223         54         36         10         3           Maximum Dose [mJ/cm²]         5600         1400         900         225         50           Writing performance - Binary         Writing performance - Binary         Writing performance - Binary         3         1         2           Minimum Eedure Size [µm]         0.5         0.7         0.8         1         2           Minimum Eedure Size [µm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3σ, nm]         40         50         60         80         110           CD Uniformity [3σ, nm]         60         70         80         130 </th <th>Write mode</th> <th>I</th> <th>II</th> <th>III</th> <th>IV</th> <th>V</th>	Write mode	I	II	III	IV	V	
Pixel Grid Grayscale [nm]	Writing performance - Grayscale						
Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         1000           Exposure Time DWL 2000 GS: For 200 mm x 200 mm [hours]         51         13.5         9         2.5         0.8           Exposure Time DWL 4000 GS: For 400 mm x 400 mm [hours]         223         54         36         10         3           Maximum Dose [mJ/cm²]         5600         1400         900         225         50           Writing performance - Binary           Minimum Feature Size [µm]         0.5         0.7         0.8         1         2           Minimum Lines and Spaces [µm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3a, nm]         40         50         60         80         110           CD Uniformity [3a, nm]         60         70         80         130         180           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         1000           System features <t< td=""><td>Overlay [3σ, nm] (over 8" x 8")</td><td></td><td></td><td>300</td><td></td><td></td></t<>	Overlay [3σ, nm] (over 8" x 8")			300			
Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         1000           Exposure Time DWL 2000 GS: For 200 mm x 200 mm (hours)         51         13.5         9         2.5         0.8           Exposure Time DWL 4000 GS: For 400 mm x 400 mm (hours)         223         54         36         10         3           Maximum Dose [mJ/cm²]         5600         1400         900         225         50           Writing performance - Binary           Minimum Feature Size [μm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3σ, nm]         40         50         60         80         110           CD Uniformity [3σ, nm]         60         70         80         130         180           Registration [3σ, nm]         12         50         75         270         870           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         1000           System features           Light source         Diode laser with 405 nm         4         4         4         4         4         4	Pixel Grid Grayscale [nm]	100	200	250	500	1000	
Exposure Time DWL 2000 GS; For 200 mm x 200 mm [hours]   51   13.5   9   2.5   0.8	Write Speed DWL 2000 GS [mm²/minute]	12	50	75	270	870	
Exposure Time DWL 4000 GS; For 400 mm x 400 mm [hours]	Write Speed DWL 4000 GS [mm²/minute]	12	50	75	270	1000	
Maximum Dose [m.J/cm²]         5600         1400         900         225         50           Writing performance - Binary           Minimum Feature Size [µm]         0.5         0.7         0.8         1         2           Minimum Lines and Spaces [µm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3a, nm]         40         50         60         80         110           CD Uniformity [3a, nm]         60         70         80         130         180           Registration [3a, nm]         200         200         100         180	Exposure Time DWL 2000 GS: For 200 mm x 200 mm [hou	urs] 51	13.5	9	2.5	0.8	
Writing performance - Binary           Minimum Feature Size [µm]         0.5         0.7         0.8         1         2           Minimum Lines and Spaces [µm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3σ, nm]         40         50         60         80         110           CD Uniformity [3σ, nm]         60         70         80         130         180           Registration [3σ, nm]         12         50         75         270         870           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         20         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         20	Exposure Time DWL 4000 GS: For 400 mm x 400 mm [hou	urs] 223	54	36	10	3	
Minimum Feature Size [μm]         0.5         0.7         0.8         1         2           Minimum Lines and Spaces [μm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3σ, nm]         40         50         60         80         110           CD Uniformity [3σ, nm]         60         70         80         130         180           Registration [3σ, nm]         12         50         75         270         870           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         20         12         80         17" x17"         17" x17	Maximum Dose [mJ/cm²]	5600	1400	900	225	50	
Minimum Lines and Spaces [μm]         0.7         0.9         1         1.5         3           Address Grid [nm]         5         10         12.5         25         50           Edge Roughness [3σ, nm]         40         50         60         80         110           CD Uniformity [3σ, nm]         60         70         80         130         180           Registration [3σ, nm]         12         50         75         270         870           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         1000           System features           Light source         Diode laser with 405 nm         75         270         1000           Maximum substrate size         DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"         1000	Writing performance - Binary						
Address Grid [nm]       5       10       12.5       25       50         Edge Roughness [30, nm]       40       50       60       80       110         CD Uniformity [30, nm]       60       70       80       130       180         Registration [30, nm]       200       200       870       870       870       870       870       870       870       870       870       870       870       870       970       870 <t< td=""><td>Minimum Feature Size [μm]</td><td>0.5</td><td>0.7</td><td>0.8</td><td>1</td><td>2</td></t<>	Minimum Feature Size [μm]	0.5	0.7	0.8	1	2	
Edge Roughness [30, nm]       40       50       60       80       110         CD Uniformity [30, nm]       60       70       80       130       180         Registration [30, nm]       200       200       87       270       870         Write Speed DWL 2000 GS [mm²/minute]       12       50       75       270       870         Write Speed DWL 4000 GS [mm²/minute]       12       50       75       270       1000         System features         Light source       Diode laser with 405 nm       80       17" x 17"       17"       1000       <	Minimum Lines and Spaces [μm]	0.7	0.9	1	1.5	3	
CD Uniformity [3σ, nm]       60       70       80       130       180         Registration [3σ, nm]       200       200       870<	Address Grid [nm]	5	10	12.5	25	50	
Registration [3σ, nm]         12         50         75         270         870           Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         1000           System features           Light source         Diode laser with 405 nm           Maximum substrate size         DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"           Substrate thickness         O to 12 mm           Maximum exposure area         DWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²           Temperature controlled environmental chamber         Temperature stability ± 0.1°, ISO 4 environment           Real-time autofocus           Optical autofocus or air-gauge autofocus           Autofocus compensation range           80 μm           System dimensions           Lithography unit (width × depth × height); weight         2350 mm × 1650 mm × 2100 mm; 3000 kg         Electroic ack (width × depth × height); weight         800 mm × 600 mm × 1800 mm; 180 kg         Installation requirements           Electroical         400 VAC ± 5 %, 50/60 Hz, 16 A         Compressed air         400 VAC ± 5 %, 50/60 Hz, 16 A         Compressed air         Compressed air         Compressed air         C	Edge Roughness [3σ, nm]	40	50	60	80	110	
Write Speed DWL 2000 GS [mm²/minute]         12         50         75         270         870           Write Speed DWL 4000 GS [mm²/minute]         12         50         75         270         1000           System features           Light source         Diode laser with 405 nm         Proper of the features         Proper of the fea	CD Uniformity [3σ, nm]	60	70	80	130	180	
Write Speed DWL 4000 GS [mm²/minute] 12 50 75 270 1000  System features  Light source Diode laser with 405 nm  Maximum substrate size DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"  Substrate thickness 0 to 12 mm  Maximum exposure area DWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²  Temperature controlled environmental chamber Temperature stability ± 0.1°, ISO 4 environment  Real-time autofocus Optical autofocus or air-gauge autofocus  Autofocus compensation range 80 µm  System dimensions  Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 600 mm × 1800 mm; 180 kg  Installation requirements  Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air 6-10 bar	Registration [3σ, nm]			200			
System featuresLight sourceDiode laser with 405 nmMaximum substrate sizeDWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"Substrate thickness0 to 12 mmMaximum exposure areaDWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²Temperature controlled environmental chamberTemperature stability ± 0.1°, ISO 4 environmentReal-time autofocusOptical autofocus or air-gauge autofocusAutofocus compensation range80 μmSystem dimensionsLithography unit (width × depth × height); weight2350 mm × 1650 mm × 2100 mm; 3000 kgElectronic rack (width × depth × height); weight800 mm × 600 mm × 1800 mm; 180 kgInstallation requirementsElectrical400 VAC ± 5 %, 50/60 Hz, 16 ACompressed air6 - 10 bar	Write Speed DWL 2000 GS [mm²/minute]	12	50	75	270	870	
Light source Diode laser with 405 nm  Maximum substrate size DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"  Substrate thickness 0 to 12 mm  Maximum exposure area DWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²  Temperature controlled environmental chamber Temperature stability ± 0.1°, ISO 4 environment  Real-time autofocus Optical autofocus or air-gauge autofocus  Autofocus compensation range 80 µm  System dimensions  Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 600 mm × 1800 mm; 1800 kg  Installation requirements  Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air 6-10 bar	Write Speed DWL 4000 GS [mm²/minute]	12	50	75	270	1000	
Maximum substrate size  DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"  Substrate thickness  0 to 12 mm  Maximum exposure area  DWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²  Temperature controlled environmental chamber  Real-time autofocus  Optical autofocus or air-gauge autofocus  Autofocus compensation range  80 µm  System dimensions  Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 600 mm × 1800 mm; 180 kg  Installation requirements  Electrical  400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air  6 - 10 bar	System features						
Substrate thickness 0 to 12 mm  Maximum exposure area DWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²  Temperature controlled environmental chamber Temperature stability ± 0.1°, ISO 4 environment  Real-time autofocus Optical autofocus or air-gauge autofocus  Autofocus compensation range 80 µm  System dimensions  Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 1800 mm; 180 kg  Installation requirements  Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air 6-10 bar	Light source	Diode laser with 405 nm					
Maximum exposure areaDWL 2000 GS: 200 x 200 mm² / DWL 4000 GS: 400 x 400 mm²Temperature controlled environmental chamberTemperature stability ± 0.1°, ISO 4 environmentReal-time autofocusOptical autofocus or air-gauge autofocusAutofocus compensation range80 μmSystem dimensionsLithography unit (width × depth × height); weight2350 mm × 1650 mm × 2100 mm; 3000 kgElectronic rack (width × depth × height); weight800 mm × 600 mm × 1800 mm; 180 kgInstallation requirements400 VAC ± 5 %, 50/60 Hz, 16 ACompressed air6 - 10 bar	Maximum substrate size	DWL 2000 GS: 9" x 9" / DWL 4000 GS: 17" x 17"					
Temperature controlled environmental chamber  Real-time autofocus  Autofocus compensation range  80 μm  System dimensions  Lithography unit (width × depth × height); weight  Electronic rack (width × depth × height); weight  Somm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight  Installation requirements  Electrical  400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air  Temperature stability ± 0.1°, ISO 4 environment  80 μm  400 μm  400 VAC ± 5 %, 50/60 Hz, 16 A  6 - 10 bar	Substrate thickness	0 to 12 mm					
Real-time autofocusOptical autofocus or air-gauge autofocusAutofocus compensation range80 μmSystem dimensionsLithography unit (width × depth × height); weight2350 mm × 1650 mm × 2100 mm; 3000 kgElectronic rack (width × depth × height); weight800 mm × 600 mm × 1800 mm; 180 kgInstallation requirements400 VAC ± 5 %, 50/60 Hz, 16 ACompressed air6 - 10 bar	Maximum exposure area	DWL 2000 GS: 200 x 200 mm <sup>2</sup> / DWL 4000 GS: 400 x 400 mm <sup>2</sup>					
Autofocus compensation range 80 µm  System dimensions  Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 600 mm × 1800 mm; 180 kg  Installation requirements  Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air 6 - 10 bar	Temperature controlled environmental chamber	Temperature stability ± 0.	Temperature stability ± 0.1°, ISO 4 environment				
Lithography unit (width × depth × height); weight 2350 mm × 1650 mm × 2100 mm; 3000 kg  Electronic rack (width × depth × height); weight 800 mm × 600 mm × 1800 mm; 180 kg  Installation requirements  Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air 6 - 10 bar	Real-time autofocus	Optical autofocus or air-gauge autofocus					
Lithography unit (width × depth × height); weight  Electronic rack (width × depth × height); weight  800 mm × 1650 mm × 2100 mm; 3000 kg  Installation requirements  Electrical  400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air  6 - 10 bar	Autofocus compensation range	80 μm					
Electronic rack (width × depth × height); weight  800 mm × 600 mm × 1800 mm; 180 kg  Installation requirements  Electrical  400 VAC ± 5 %, 50/60 Hz, 16 A  Compressed air  6 - 10 bar	System dimensions						
Installation requirementsElectrical400 VAC ± 5 %, 50/60 Hz, 16 ACompressed air6 - 10 bar	Lithography unit (width × depth × height); weight	2350 mm × 1650 mm × 2100 mm; 3000 kg					
Electrical 400 VAC ± 5 %, 50/60 Hz, 16 A Compressed air 6 - 10 bar	Electronic rack (width × depth × height); weight	800 mm × 600 mm × 1800 mm; 180 kg					
Compressed air 6 - 10 bar	Installation requirements						
	Electrical	$400 \text{ VAC} \pm 5 \%$ , $50/60 \text{ Hz}$ ,	400 VAC ± 5 %, 50/60 Hz, 16 A				
Cleanroom ISO 6 or better recommended	Compressed air	6 - 10 bar	6 - 10 bar				
	Cleanroom	ISO 6 or better recommen	ded				

**Please note:** Specifications depend on individual process conditions and may very according to equipment configuration. Write speed depends on exposure area. Design and specifications are subject to change without prior notice.



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